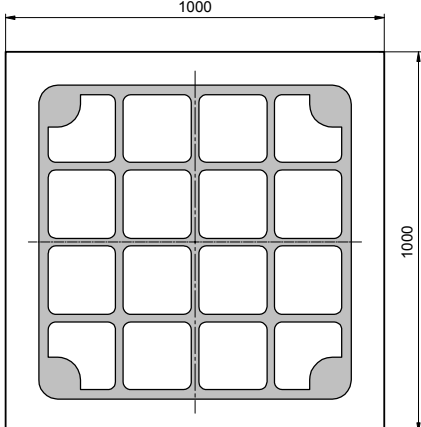


Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	P (anode) up

 <p>PoC-05</p>	typ. dimensions ( $\mu\text{m}$ )
	<u>typ. thickness</u> 150 ( $\pm 25$ ) $\mu\text{m}$  <u>cathode</u> gold alloy, 0.5 $\mu\text{m}$  <u>anode</u> gold alloy, 1.5 $\mu\text{m}$

### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		1.15		V
Forward voltage <sup>2</sup>	$I_F = 350 \text{ mA}$	$V_F$		1.35		V
Reverse voltage	$I_R = 10 \mu\text{A}$	$V_R$	5			V
Radiant power <sup>1</sup>	$I_F = 20 \text{ mA}$	$\Phi_e$		1.5		mW
Radiant power <sup>2</sup>	$I_F = 350 \text{ mA}$	$\Phi_e$		22.5		mW
Radiant intensity <sup>1</sup>	$I_F = 20 \text{ mA}$	$I_e$		0.45		mW/sr
Radiant intensity <sup>2</sup>	$I_F = 350 \text{ mA}$	$I_e$		7.3		mW/sr
Peak wavelength	$I_F = 20 \text{ mA}$	$\lambda_P$	900	910	920	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		60		nm
Switching time	$I_F = 20 \text{ mA}$	$t_r, t_f$		20		ns

<sup>1</sup>Measured on bare chip on TO-18 header

<sup>2</sup>Measured on bare chip glued on a  $\varnothing 8 \times 1 \text{ mm}$  Cu header (10 s after switched on) (for information only)

### Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-910-11				

**Packing:** Chips on adhesive film with wire-bond side on top

\*Note: All measurements carried out on *EPIGAP* equipment